

PSMN1R8-30BL

N-channel 30 V, 1.8 mΩ logic level MOSFET in D2PAK Rev. 1 — 22 March 2012

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	270	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>		-	2.17	2.6	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>		-	1.55	1.8	mΩ
Dynamic o	characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 15 \text{ V};$		-	22	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15		-	83	-	nC
	ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω ; unclamped		-	-	1.1	J

^[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

	•	<u> </u>		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R8-30BL	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R8-30BL	PSMN1R8-30BL

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; see Figure 3		-	1120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	270	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode					
Is	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1120	Α
Avalanche ru	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω ; unclamped		-	1.1	J

[1] Continuous current is limited by package.

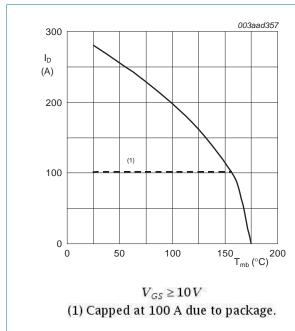
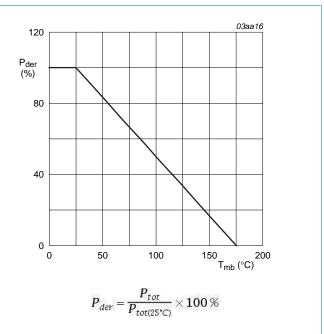


Fig 1. Continuous drain current as a function of mounting base temperature

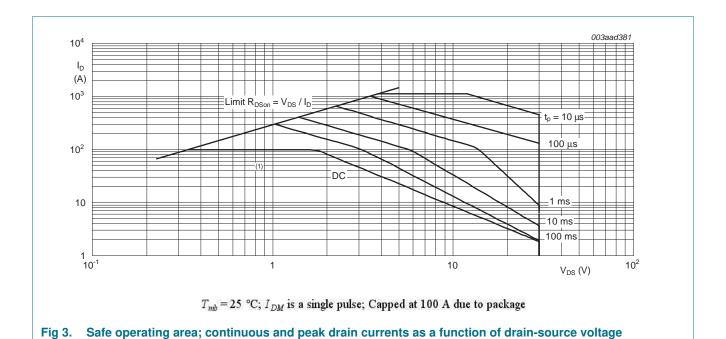


g 2. Normalized total power dissipation as a function of mounting base temperature

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

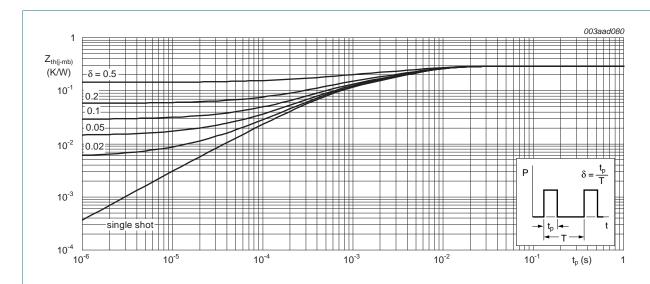


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

N-channel 30 V, 1.8 mΩ logic level MOSFET in D2PAK

Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see Figure 10; see Figure 11	1.3	1.7	2.15	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11	0.5	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 11	-	-	2.45	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	4	μΑ
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 125 °C	-	-	200	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon} drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	1.82	2.1	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 °C;$ see Figure 13; see Figure 12	-	2.95	3.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 13; see Figure 12	-	2.17	2.6	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	1.55	1.8	mΩ
R _G	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic o	characteristics					
Q _{G(tot)}	Q _{G(tot)} total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	170	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	158	-	nC
		I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V;	-	83	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	29	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	17	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	12	-	nC
Q_{GD}	gate-drain charge		-	22	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.6	-	V
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	10180	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	2000	-	pF
C _{rss}	reverse transfer capacitance		-	872	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	92	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	156	-	ns
$t_{d(off)}$	turn-off delay time		-	135	-	ns
t _f	fall time		-	69	-	ns
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Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	in diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.7	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	64	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	60	-	nC

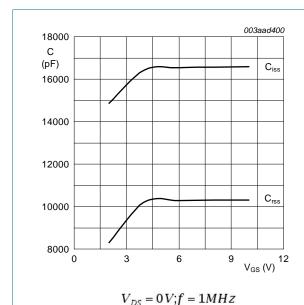
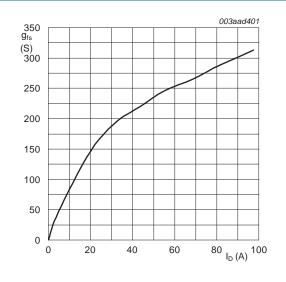


Fig 5. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 15V$

Fig 6. Forward transconductance as a function of drain current; typical values

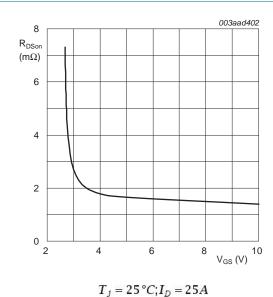
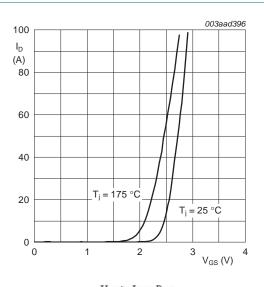


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$

Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

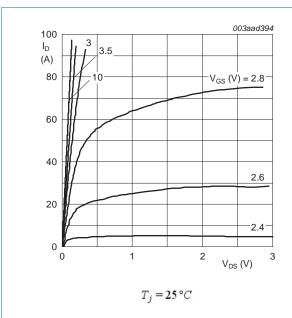


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

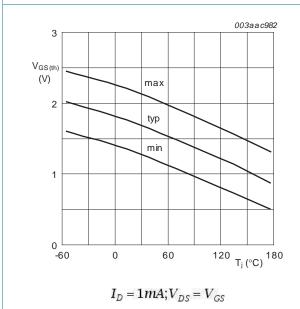
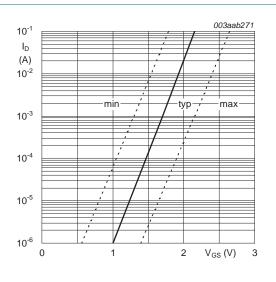


Fig 11. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

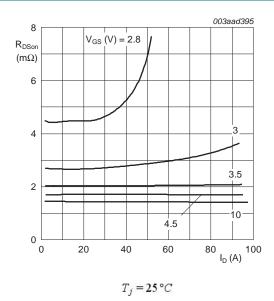


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

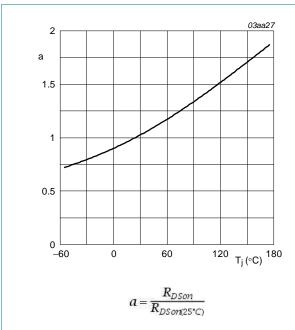


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

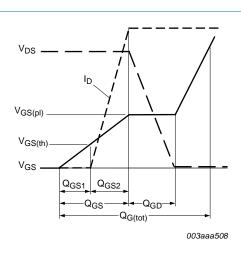


Fig 14. Gate charge waveform definitions

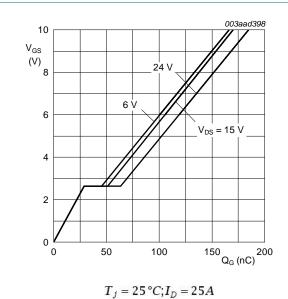
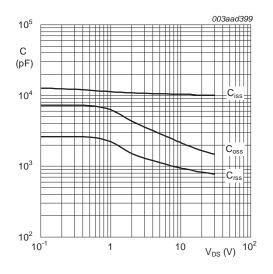
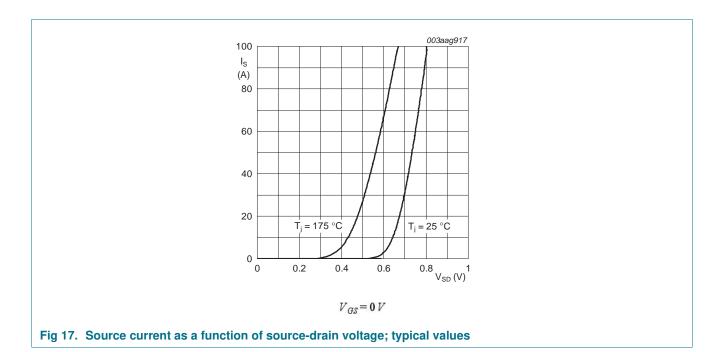


Fig 15. Gate-source voltage as a function of gate charge; typical values



$$V_{GS} = 0V; f = 1MHz$$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



8. Package outline

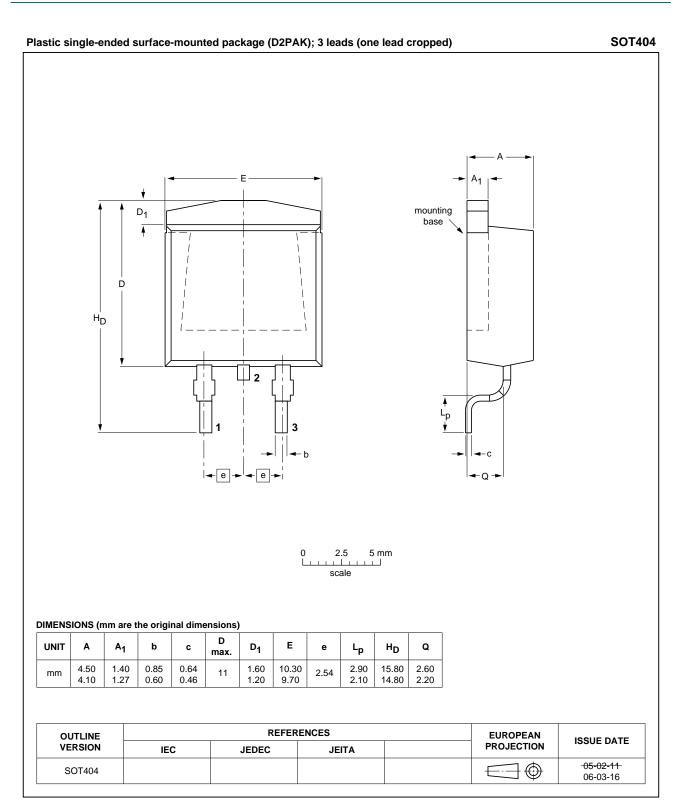


Fig 18. Package outline SOT404 (D2PAK)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R8-30BL v.1	20120322	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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